



SILICON SCHOTTKY POWER RECTIFIER 40 A, 100 V

Qualified per MIL-PRF-19500/679

DESCRIPTION

This low-profile 1N6844U3 Schottky rectifier device is military qualified up to a JANTXV level for high-reliability applications. Microsemi also offers numerous other products to meet higher and lower power voltage regulation applications.

Important: For the latest information, visit our website http://www.microsemi.com.

FEATURES

- Surface mount equivalent of JEDEC registered 1N6844.
- Low profile ceramic SMD.
- JAN, JANTX, JANTXV qualifications available per MIL-PRF-19500/679.
- RoHS compliant versions available (commercial grade only).

APPLICATIONS / BENEFITS

- High surge rating.
- Low reverse leakage current.
- Low forward voltage.
- Seam welded package.
- Low capacitance.
- Ultrasonic aluminum wire bonds.

MAXIMUM RATINGS @ $T_c = +25 \,^{\circ}C$ unless otherwise noted

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	$T_{\rm J}$ and $T_{\rm STG}$	-65 to +150	°C
Thermal Resistance Junction-to-Ambient	R _{ÐJA}	40	°C/W
Thermal Resistance Junction-to-Case	R _{eJC}	2.0	°C/W
(1.6 °C/W maximum)			
Working Peak Reverse Voltage	V _{RWM}	100	V
Junction Capacitance	CJ	600	pF
Average DC Output Current @ T _C = +125 °C	lo	15	А
Non-Repetitive Sinusoidal Surge Current @ tp = 8.3 ms	I _{FSM}	250	А

MSC – Lawrence

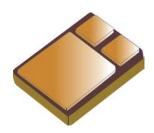
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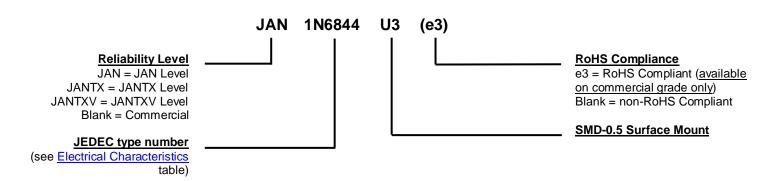
U3 (SMD-0.5) Package



MECHANICAL and PACKAGING

- CASE: Ceramic and gold over nickel plated steel.
- TERMINALS: Gold over nickel plated tungsten/copper.
- MARKING: Part number, date code, A = anode.
- POLARITY: See <u>schematic</u> on last page.
- WEIGHT: 0.9 grams.
- See <u>Package Dimensions</u> on last page.

PART NOMENCLATURE



SYMBOLS & DEFINITIONS				
Symbol	Definition			
CJ	Junction Capacitance: The junction capacitance in pF at a specified frequency (typically 1MHz) and specified voltage.			
١ _F	Forward Current: The forward current dc value, no alternating component.			
I _R	Reverse Current: The maximum reverse (leakage) current that will flow at the specified voltage and temperature.			
TJ	Junction Temperature: The temperature of a semiconductor junction.			
V _F	Forward Voltage: The forward voltage the device will exhibit at a specified current (typically shown as maximum value).			
V _R	Reverse Voltage: The reverse voltage dc value, no alternating component.			



Parameters / Test Conditions	Symbol	Min.	Max.	Unit
OFF CHARACTERTICS				
Forward Voltage* $I_F = 5 A$ $I_F = 15 A$ $I_F = 20 A$ $I_F = 5 A, T_C = -55 °C$ $I_F = 5 A, T_C = +125 °C$ $I_F = 15 A, T_C = +125 °C$	V _F		0.70 0.90 1.00 0.85 0.58 0.72	V
Reverse Current $V_R = 100 V$ $V_R = 100 V$, $T_C = +125 °C$	I _R		0.100	mA
Junction Capacitance $V_R = 5 V$ f = 1 MHz $V_{SIG} = 50 mV (p-p)$	CJ		600	pF

ELECTRICAL CHARACTERISTICS @ T_A = +25°C unless otherwise noted

 * Pulse test: Pulse width 300 $\mu sec,$ duty cycle 2%.





GRAPHS

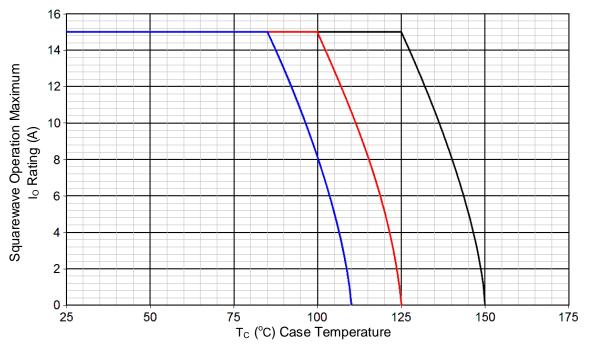


FIGURE 1 Temperature-Current Derating

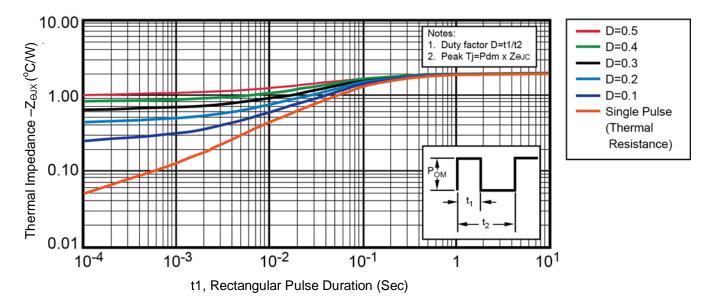
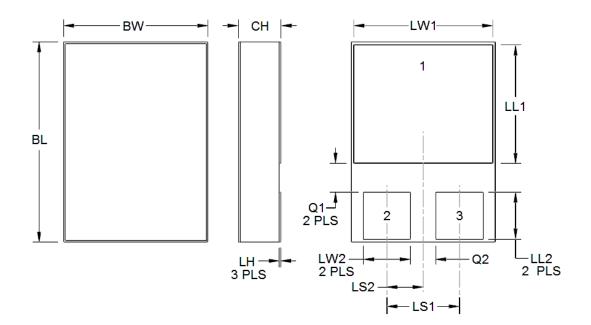


FIGURE 2 Thermal Impedance



PACKAGE DIMENSIONS



NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- 3. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.



Schematic

Symbol	DIMENSIONS			
	INCH		MILLIMETERS	
	Min	Max	Min	Max
BL	.395	.405	10.03	10.29
BW	.291	.301	7.39	7.65
СН	.112	.124	2.84	3.15
LH	.010	.020	0.25	0.51
LL1	.220	.230	5.59	5.84
LL2	.115	.125	2.92	3.18
LS1	.150 BSC		3.81 BSC	
LS2	.075 BSC		1.91 BSC	
LW1	.281	.291	7.14	7.39
LW2	.090	.100	2.29	2.54
Q1	.030		0.76	
Q2	.030		0.76	
Term 1	Cathode			
Term 2	Anode (See Schematic)			
Term 3	Anode (See Schematic)			